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(54) Title: METHOD FOR FABRICATING A SOLAR CELL USING A DIRECT-PATTERN PIN-HOLE-FREE MASKING LAYER

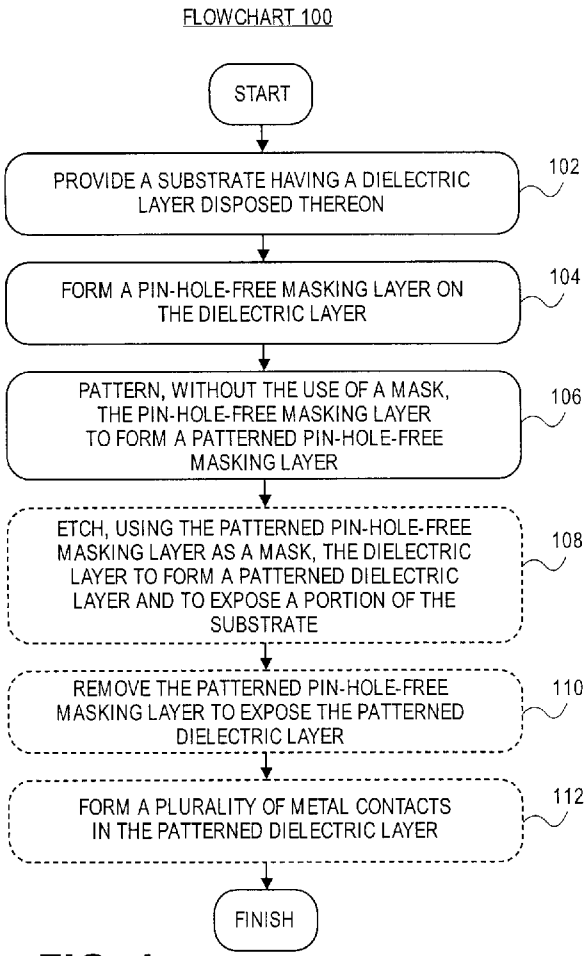


FIG. 1

(57) Abstract: A method for fabricating a solar cell is described. The method includes first providing a substrate having a dielectric layer disposed thereon. A pin-hole-free masking layer is then formed above the dielectric layer. Finally, without the use of a mask, the pin-hole-free masking layer is patterned to form a patterned pin-hole-free masking layer.

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